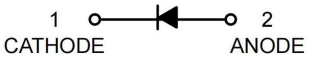
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BAS16XV2T1G
Switching Diode

Features

- High−Speed Switching Applications
- Lead Finish: 100% Matte Sn (Tin)
- Qualified Reflow Temperature: 260°C
- Extremely Small SOD−523 Package
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant





SOD−523

MARKING DIAGRAM



A6 = Specific Device Code
M = Date Code
▪ = Pb−Free Package

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	100	V
Continuous Forward Current	I_F	200	mA
Peak Forward Surge Current	$I_{FM(surge)}$	500	mA
Repetitive Peak Forward Current (Pulse Wave = 1 sec, Duty Cycle = 66%)	I_{FRM}	500	mA
Non−Repetitive Peak Forward Current (Square Wave, T_J = 25°C prior to surge) t = 1 μs t = 1 ms t = 1 s	I_{FSM}	 4.0 1.0 0.5	A

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, (Note 1) T_A = 25°C Derate above 25°C	P_D	200 1.57	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	635	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to 150	°C

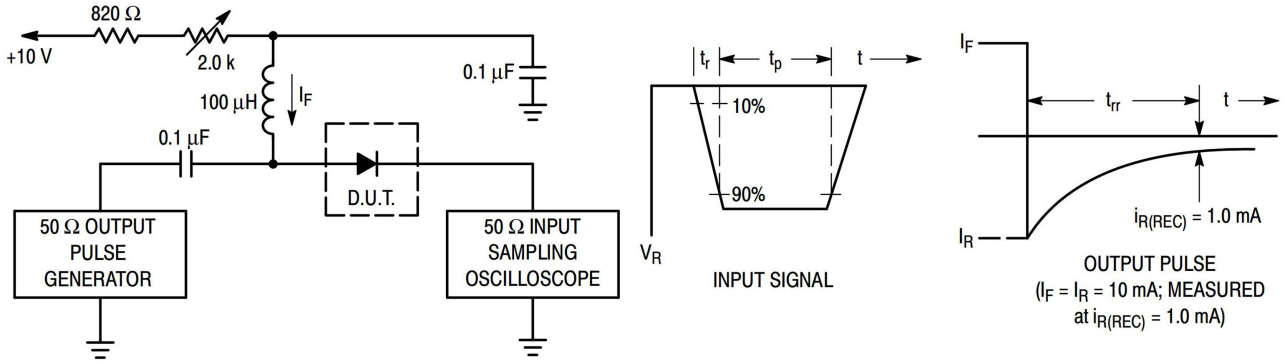
1. FR-5 Minimum Pad.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Voltage Leakage Current (V_R = 100 V) (V_R = 75 V, T_J = 150°C) (V_R = 25 V, T_J = 150°C)	I_R	 – – –	 1.0 50 30	μA
Reverse Breakdown Voltage (I_{BR} = 100 μA)	$V_{(BR)}$	100	–	V
Forward Voltage (I_F = 1.0 mA) (I_F = 10 mA) (I_F = 50 mA) (I_F = 150 mA)	V_F	 – – – –	 715 855 1000 1250	mV
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_D	–	2.0	pF
Forward Recovery Voltage (I_F = 10 mA, t_r = 20 ns)	V_{FR}	–	1.75	V
Reverse Recovery Time (I_F = I_R = 10 mA, R_L = 50 Ω)	t_{rr}	–	6.0	ns
Stored Charge (I_F = 10mA to V_R = 5.0V, R_L = 500 Ω)	Q_S	–	45	pC



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

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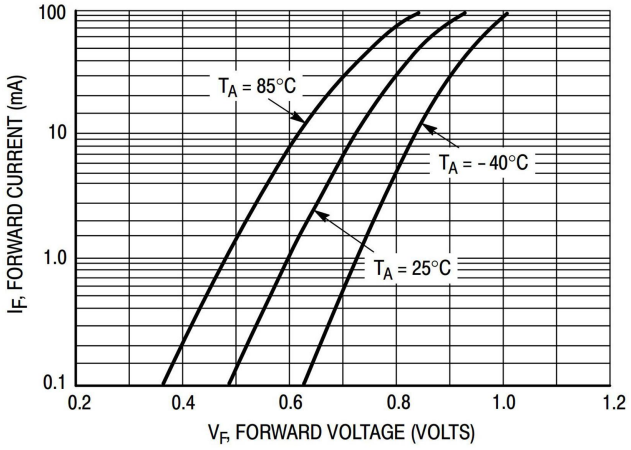


Figure 2. Forward Voltage

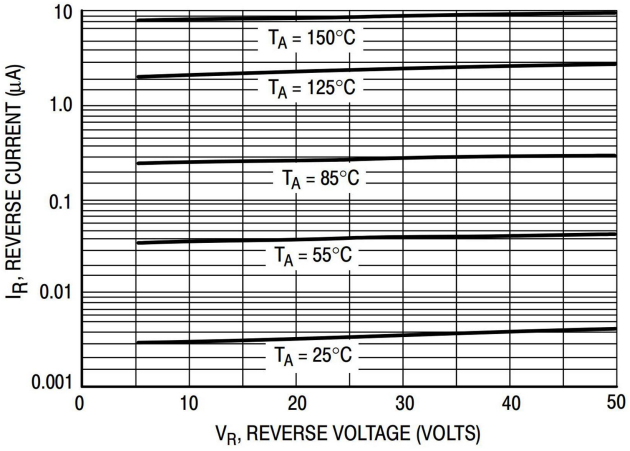


Figure 3. Leakage Current

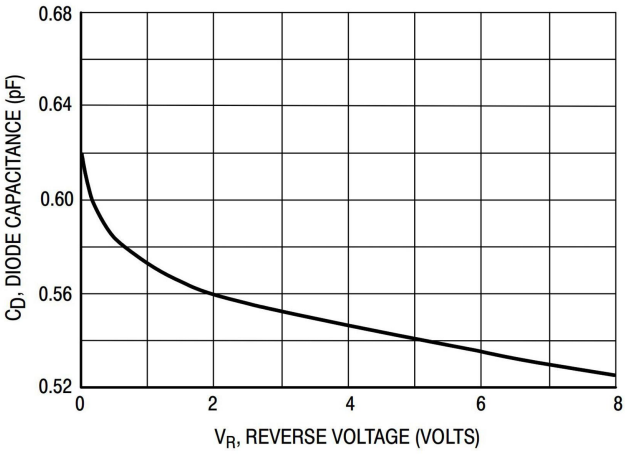


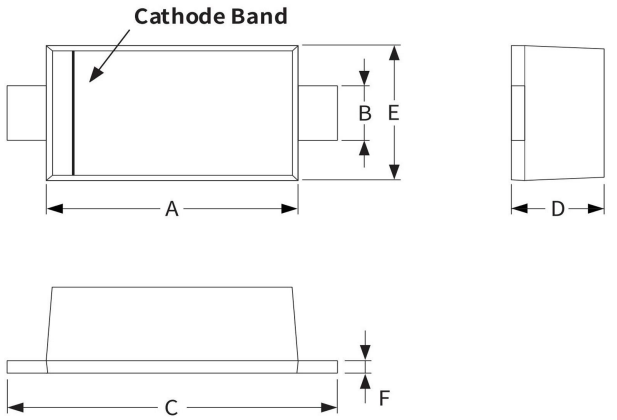
Figure 4. Capacitance

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Ordering Information

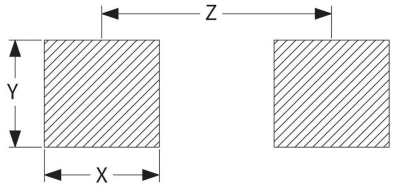
PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOD-523	R1	0.002	3000	30000	240000	7"

Package Outline Dimensions (SOD-523)



Symbol	Dimensions			
	Millimeters		Inches	
	Min	Max	Min	Max
A	1.10	1.30	0.043	0.051
B	0.25	0.35	0.010	0.014
C	1.50	1.70	0.059	0.067
D	0.50	0.70	0.020	0.027
E	0.70	0.90	0.027	0.035
F	0.05	0.20	0.002	0.008

Suggested Pad Layout



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
X	0.55	0.65	0.022	0.026
Y	0.65	0.75	0.026	0.029
Z	1.37	1.47	0.054	0.058